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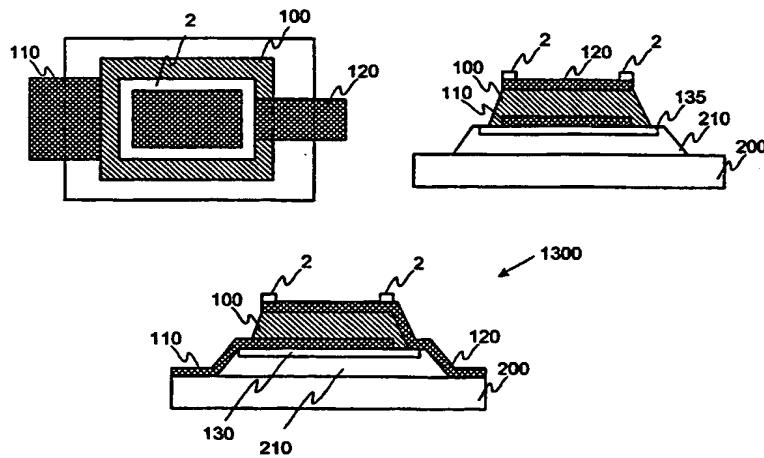
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(54) Title: RESONATOR STRUCTURE AND A FILTER COMPRISING SUCH A RESONATOR STRUCTURE



(57) Abstract: A resonator structure (1200, 1300, 1400), where a certain wave mode is piezoelectrically excitable, comprises at least two conductor layers (110, 120) and at least one piezoelectric layer (110) in between the conductor layers, said conductor layers and piezoelectric layer extending over a first area of the resonator structure, which first area is a piezoelectrically excitable area of the resonator structure. The resonator structure is characterized in that it comprises a frame-like zone (2, 4) confining a center area (3) within the first area, a cut-off frequency of the piezoelectrically excited wave mode in the layer structure of the frame-like zone is different from that in the layer structure of the center area, and width of the frame-like zone and acoustical properties of the layer structure in the frame-like zone are arranged so that displacement relating to the piezoelectrically excited strongest resonance mode is substantially uniform in the center area of the resonator.

WO 01/06647 A1